

<b>SANYO</b>	No.4308	<b>2SJ288</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

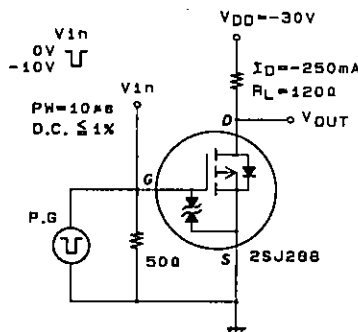
			unit
Drain to Source Voltage	$V_{DS}$	-60	V
Gate to Source Voltage	$V_{GS}$	$\pm 15$	V
Drain Current(DC)	$I_D$	-500	mA
Drain Current(Pulse)	$I_{DP}$	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	A
Allowable Power Dissipation	$P_D$	$T_c = 25^\circ C$	3.5 W
		Mounted on ceramic board (250mm <sup>2</sup> × 0.8mm)	1.3 W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

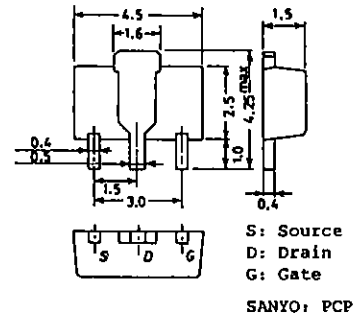
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60V, V_{GS} = 0$			-100	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -250mA$	240	400		mS
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -250mA, V_{GS} = -10V$		2.2	3.0	$\Omega$
	$R_{DS(on)}$	$I_D = -250mA, V_{GS} = -4V$		3.0	4.0	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20V, f = 1MHz$		45		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20V, f = 1MHz$		20		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20V, f = 1MHz$		5		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7		ns
Rise Time	$t_r$	"		10		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		35		ns
Fall Time	$t_f$	"		20		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -500mA, V_{GS} = 0$		-1		V

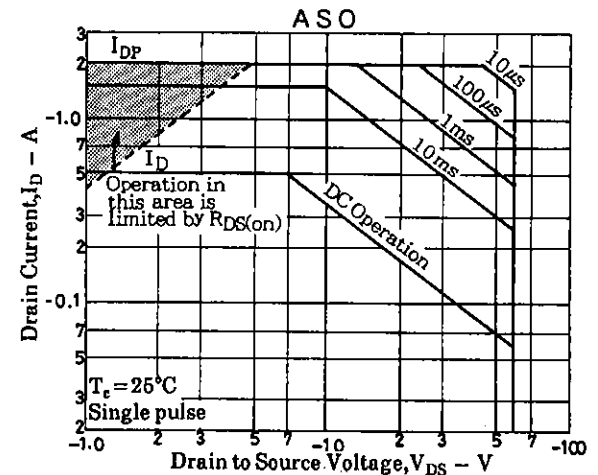
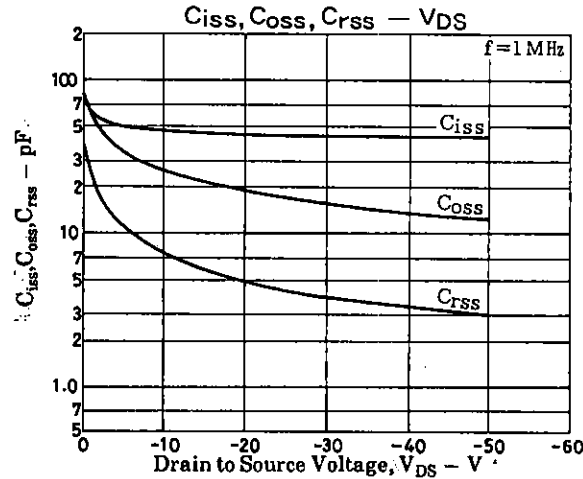
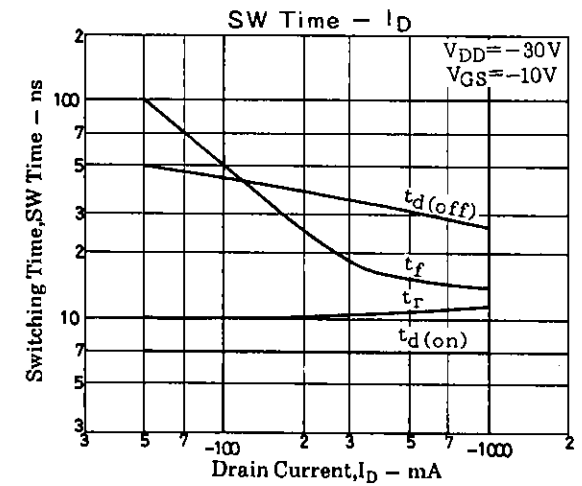
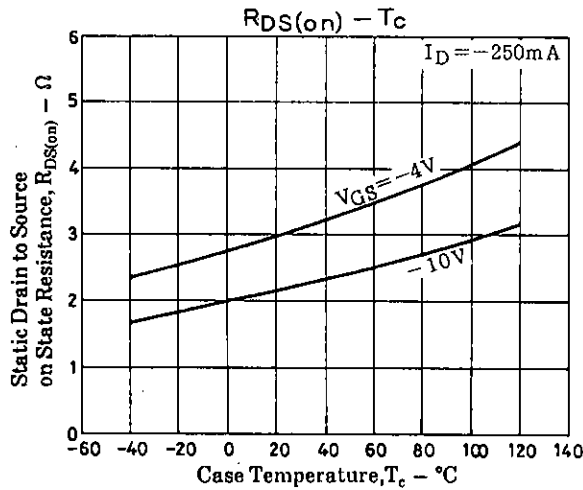
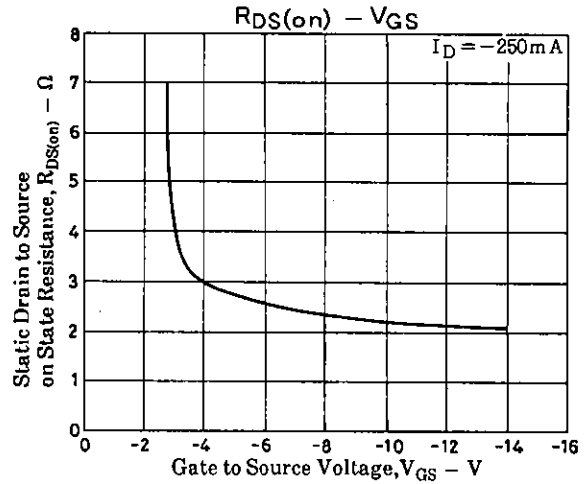
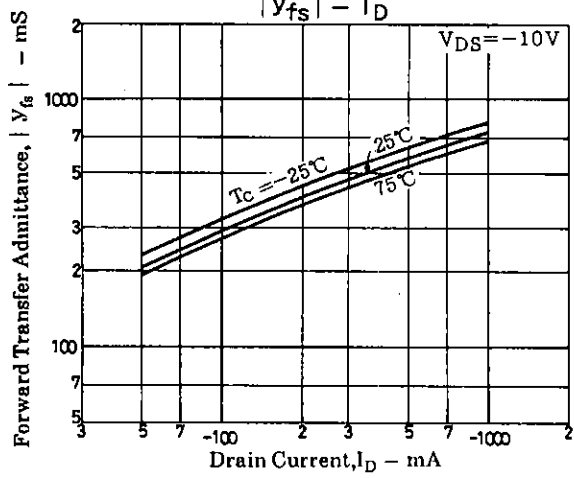
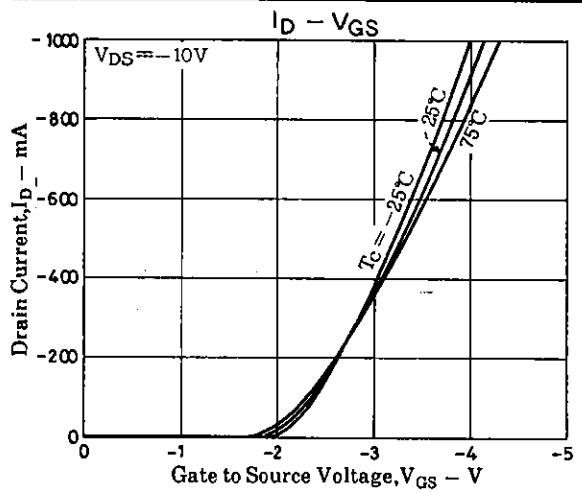
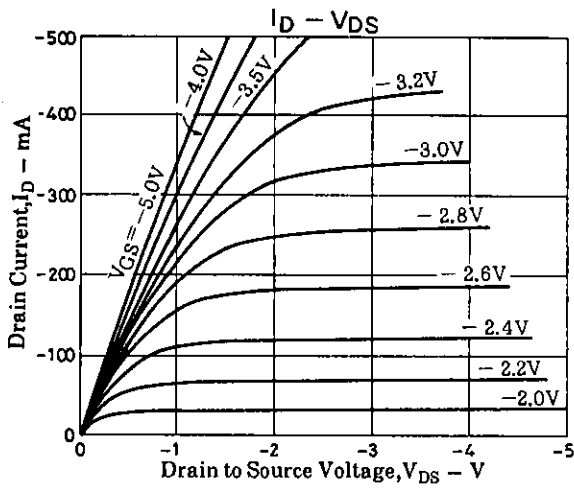
Marking : JE

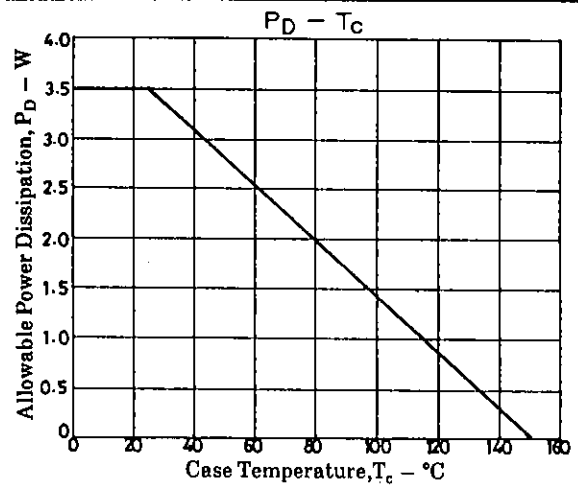
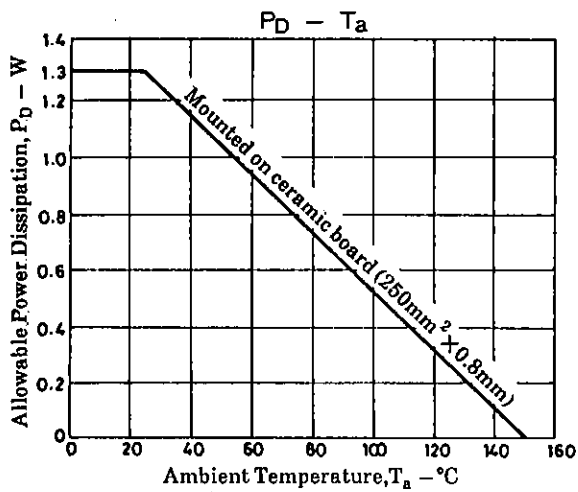
**Switching Time Test Circuit**



**Package Dimensions 2062 (unit : mm)**







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